Converter Topologies Using High-Voltage High-Frequency SiC Devices

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Medium-Voltage Levels and Applications



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- 1. Cascade Multilevel Converters (Both Star- and Delta-CMI): STATCOM, ESS, UPFC, ...
- 2. Modular Multilevel Converter (MMC): HVDC
- 3. Emerging Multilevel Converters (2-Port CMI, nX Converter, ...)

Example 1: Power Flow Controller at 13.8 kV





Si IGBT based VSC for HVDC and FACTS:

- Consider the case of Trans-Bay Cable, CA for example
- Built on modular multi-level converter topology
- Two Converters
- Each converter consists of 6 legs
- Each leg consists of ~200 modules*



Fig. 1. Topology of a Modular Multilevel Converter based Scheme

*Teeuwsen, S.P., "Modeling the Trans Bay Cable Project as Voltage-Sourced Converter with Modular Multilevel Converter design," Power and Energy Society General Meeting, 2011 IEEE, vol., no., pp.1,8, 24-29 July 2011

Example 1: How many modules are required to achieve the needed performance?



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Example 2: Today's Si-based HVDC MMC converter

- Typical Service life of an overall system is 30 years*.
- All modules in a leg are in series.
- Without redundancy for 200 modules in series, each module has to be designed for an impossible lifetime of 200 X 30 = 6,000 years!
- Redundant modules are needed to make 30-year service time possible and to improve reliability.
- Large redundancy is needed to achieve 30-year lifetime.
- *Peter Kohnstam, Siemens High Voltage DC Conversion Systems- 22 April 2013, United States Department of Energy

Benefits Of SiC Power Devices

Today's Si IGBT voltage ratings*:

1700 V/ 3600 A to 6500 V/ 750 A

With wide band gap devices, high current, high voltage devices are possible.

- 20-kV device are possible, which leads to reduction in the number of series modules for the same CMI or MMC rating.
- Low redundancy is needed to achieve 30-year lifetime, thus the number of total modules becomes significantly lower.
- Higher efficiency, simpler system, longer lifetime.

*Ultra High Voltage Semiconductor Power Devices for Grid Applications -

M. T. Rahimo IEDM, December 2010, San Franscisco, USA

Benefits Of SiC Power Devices -cont

SiC power device

- Improves reliability of operation due to lesser number of redundant sub-modules.
- Reduces component costs.
- Increases efficiency of CMI and MMC converters.
- Reduces cooling requirement, potentially making natural convection air cool possible –A utility company's dream!

New Converter Topologies and Applications Become Feasible Because of SiC's High-Frequency Switching

- Solid-State Variable Inductor
- Solid-State Variable Capacitor
- Solid-State Variable Transformer
- DC Transformer, nX DC-DC Converter
- DC Capacitor-less Inverters
- Z-Source Converters

For Solar Power Generation

For example: MW MV solar power based on cascade multilevel and quasi-Z-Source Inverter

- High switching frequency → small inductors
- High temp. → minimum cooling



Ideal Grid Converters/Inverters

